FLAT-BASE TYPE INSULATED PACKAGE

PM450CLA060



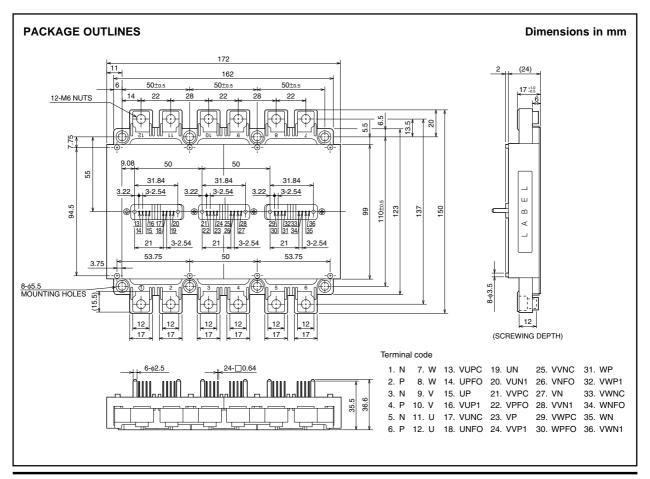
FEATURE

- a) Adopting new 5th generation IGBT (CSTBT) chip, which performance is improved by $1\mu m$ fine rule process. For example, typical Vce(sat)=1.8V @Tj=125°C
- b) I adopt the over-temperature conservation by Tj detection of CSTBT chip, and error output is possible from all each conservation upper and lower arm of IPM.
- 3¢ 450A, 600V Current-sense IGBT type inverter
- Monolithic gate drive & protection logic
- · Detection, protection & status indication circuits for, shortcircuit, over-temperature & under-voltage (Fo available from all arm devices)
- · Acoustic noise-less 37kW class inverter application
- UL Recognized Yellow Card No.E80276(N)

File No.E80271

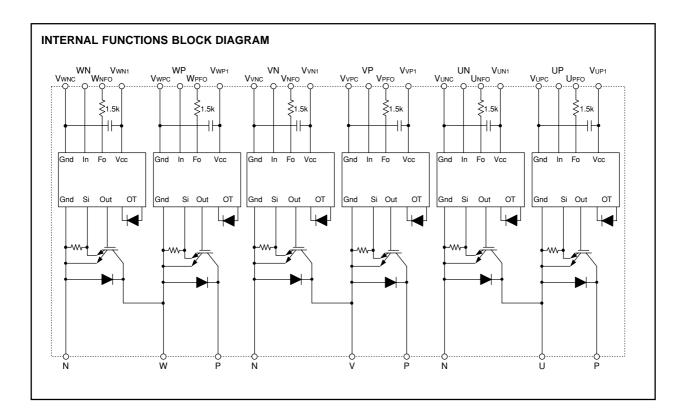
APPLICATION

General purpose inverter, servo drives and other motor controls





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MAXIMUM RATINGS (Tj = 25° C, unless otherwise noted)

INVERTER PART

Symbol	Parameter	Condition	Ratings	Unit
VCES	Collector-Emitter Voltage	VD = 15V, VCIN = 15V	600	V
±IC	Collector Current	Tc = 25°C	450	Α
±ICP	Collector Current (Peak)	Tc = 25°C	900	Α
Pc	Collector Dissipation	$Tc = 25^{\circ}C$ (Note-1)	1041	W
Tj	Junction Temperature		-20 ~ +150	°C

CONTROL PART

Symbol	Parameter	Condition	Ratings	Unit
VD	Supply Voltage	Applied between: VuP1-VuPc, VvP1-VvPc, VwP1-VwPc	20	V
VD	Supply Voltage	VUN1-VUNC, VVN1-VVNC, VWN1-VWNC	20	V
VCIN	Input Voltage	Applied between: UP-VUPC, VP-VVPC, WP-VWPC	20	V
VCIN		Un-Vunc, Vn-Vvnc, Wn-Vwnc	20	٧
VFO	Fault Output Supply Voltage	Applied between: UPFO-VUPC, VPFO-VVPC, WPFO-VWPC	20	V
VFO		UNFO-VUNC, VNFO-VVNC, WNFO-VWNC	20	٧
IFO	Fault Output Current	Sink current at UPFO, VPFO, WPFO, UNFO, VNFO, WNFO	00	A
		terminals	20	mA

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TOTAL SYSTEM

Symbol	Parameter	Condition	Ratings	Unit
VCC(PROT)	Supply Voltage Protected by SC	VD = 13.5 \sim 16.5V, Inverter Part, Tj = +125 $^{\circ}$ C Start	400	V
VCC(surge)	Supply Voltage (Surge)	Applied between : P-N, Surge value	500	V
Tstg	Storage Temperature		− 40 ~ +125	°C
Viso	Isolation Voltage	60Hz, Sinusoidal, Charged part to Base, AC 1 min.	2500	Vrms

THERMAL RESISTANCES

	_	Condition		Limits			
Symbol	Parameter			Тур.	Max.	Unit	
Rth(j-c)Q	Junction to case Thermal	Inverter IGBT (per 1 element) (Note-1)	_	_	0.12		
Rth(j-c)F	Resistances	Inverter FWDi (per 1 element) (Note-1)	_	_	0.19	0C/M	
Rth(c-f)	Contact Thermal Resistance	Case to fin, (per 1 module)		_	0.014	°C/W	
		Thermal grease applied (Note-1)	-				

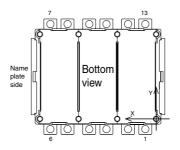
(Note-1) Tc measurement point is just under the chip.

If you use this value, Rth(f-a) should be measured just under the chips.

Table 1: Tc (under the chip) measurement point is below.

(Unit:mm)

ſ	arm	U	Р	V	Р	W	/P	U	N	V	N	W	N.
L	axis	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi	IGBT	FWDi
Ī	Х	26.5	23.9	76.5	73.9	126.5	123.9	23.4	26.0	73.4	76.0	123.4	126.0
	Υ	85.5	70.5	85.5	70.5	85.5	70.5	24.5	39.5	24.5	39.5	24.5	39.5



ELECTRICAL CHARACTERISTICS (Tj = 25° C, unless otherwise noted) **INVERTER PART**

	Parameter Condition				Unit		
Symbol	Parameter	Condition	Condition		Тур.	Max.	Ullit
VCE(sat)	Collector-Emitter	VD = 15V, IC = 450A	Tj = 25°C	_	1.7	2.2	W
	Saturation Voltage	VCIN = 0V (Fig. 1)	Tj = 125°C	_	1.8	2.3	V
VEC	FWDi Forward Voltage	-IC = 450A, VD = 15V, VCIN = 15V	(Fig. 2)	_	2.6	3.7	V
ton		\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		0.5	1.0	2.4	
trr		VD = 15V, VCIN = 0V↔15V		_	0.2	0.4	
tc(on)	Switching Time	Vcc = 300V, Ic = 450A		_	0.4	1.0	μs
toff		Tj = 125°C	(Fir. 0. 4)	_	2.2	3.5	
tc(off)		Inductive Load	(Fig. 3, 4)	_	0.6	1.1	
loco	Collector-Emitter	Voc Voca Vous 15V (Fig. 5)	Tj = 25°C	_	_	1	A
ICES	Cutoff Current	VCE = VCES, VCIN = 15V (Fig. 5)	Tj = 125°C	_	_	10	mA

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CONTROL PART

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Symbol	Parameter	Condition	Condition		Тур.	Max.	Unit
ID	Circuit Current	VD = 15V. VCIN = 15V	V*N1-V*NC	_	11	18	4
l in	Circuit Current	VD = 13V, VCIN = 13V	V*P1-V*PC	_	11	18	mA
Vth(ON)	Input ON Threshold Voltage	Applied between: UP-VUPC, VP-VVPC, V	WP-VWPC	1.2	1.5	1.8	V
Vth(OFF)	Input OFF Threshold Voltage	Un-Vunc, Vn-Vvnc, V	Wn-Vwnc	1.7	2.0	2.3	
SC	Short Circuit Trip Level	$-20 \le T_j \le 125^{\circ}C, V_D = 15V$	(Fig. 3,6)	900	_	_	Α
toff(SC)	Short Circuit Current Delay Time	VD = 15V	(Fig. 3,6)	_	0.2	_	μs
ОТ	Over Temperature Protection	VD = 15V	Trip level	135	145	_	°C
OTr	Over Temperature Protection	Detect Tj of IGBT chip	Reset level	_	125	_	
UV	Supply Circuit Under-Voltage	–20 ≤ T _i ≤ 125°C	Trip level	11.5	12.0	12.5	V
UVr	Protection	-20 ± 1j ± 125 0	Reset level	_	12.5	_	
IFO(H)	Fault Output Current	VD = 15V. VFO = 15V	(Note-2)	_	_	0.01	mA
IFO(L)	Fault Output Current	VD = 13V, VFO = 13V	(14016-2)	_	10	15	'''^
tFO	Minimum Fault Output Pulse Width	VD = 15V	(Note-2)	1.0	1.8	_	ms

(Note-2) Fault output is given only when the internal SC, OT & UV protections schemes of either upper or lower arm device operate to protect it.

MECHANICAL RATINGS AND CHARACTERISTICS

	Б	Condition			Unit		
Symbol Parameter		Condition		Min.	Тур.	Max.	Unit
_	Mounting torque	Main terminal	screw: M6	3.5	4.0	4.5	N•m
_	Mounting torque	Mounting part	screw: M5	2.5	3.0	3.5	N•m
_	Weight	_		_	1250	_	g

RECOMMENDED CONDITIONS FOR USE

Symbol	Parameter	Condition	Recommended value	Unit
Vcc	Supply Voltage	Applied across P-N terminals	≤ 400	V
VD	Control Supply Voltage	Applied between: VuP1-VuPc, VvP1-VvPc, VwP1-VwPc VuN1-VuNc, VvN1-VvNc, VwN1-VwNc (Note-3)	15 ± 1.5	V
VCIN(ON)	Input ON Voltage	Applied between : UP-VUPC, VP-VVPC, WP-VWPC	≤ 0.8	V
VCIN(OFF)	Input OFF Voltage	Un-Vunc, Vn-Vvnc, Wn-Vwnc	≥ 9.0	
fPWM	PWM Input Frequency	Using Application Circuit of Fig. 8	≤ 20	kHz
tdead	Arm Shoot-through Blocking Time	For IPM's each input signals (Fig. 7)	≥ 3.0	μs

(Note-3) With ripple satisfying the following conditions: dv/dt swing $\leq \pm 5V/\mu s$, Variation $\leq 2V$ peak to peak

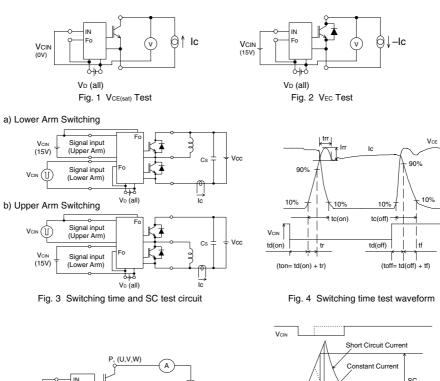


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PRECAUTIONS FOR TESTING

- Before appling any control supply voltage (VD), the input terminals should be pulled up by resistores, etc. to their corresponding supply voltage and each input signal should be kept off state.
 After this, the specified ON and OFF level setting for each input signal should be done.
- 2. When performing "SC" tests, the turn-off surge voltage spike at the corresponding protection operation should not be allowed to rise above VCEs rating of the device.

(These test should not be done by using a curve tracer or its equivalent.)



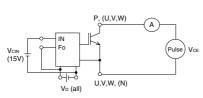


Fig. 5 Ices Test

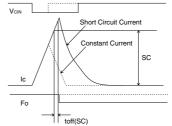
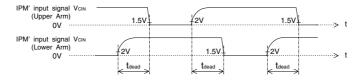


Fig. 6 SC test waveform



1.5V: Input on threshold voltage Vth(on) typical value, 2V: Input off threshold voltage Vth(off) typical value

Fig. 7 Dead time measurement point example



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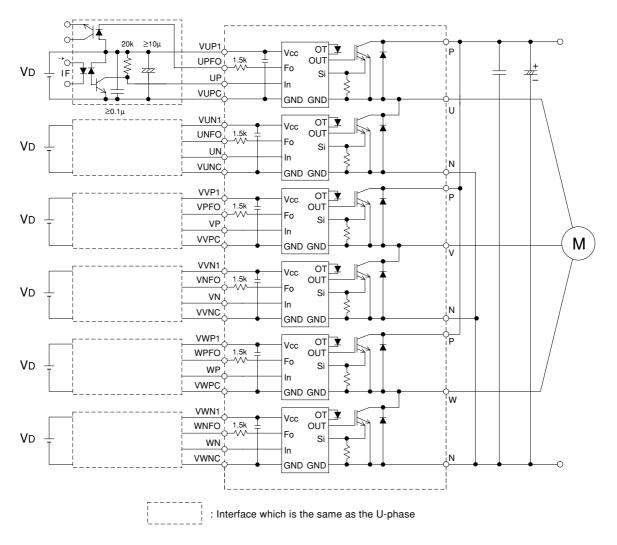


Fig. 8 Application Example Circuit

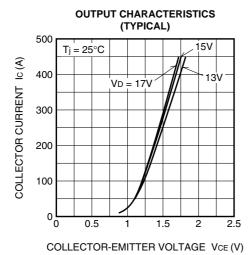
NOTES FOR STABLE AND SAFE OPERATION;

- Design the PCB pattern to minimize wiring length between opto-coupler and IPM's input terminal, and also to minimize the stray capacity between the input and output wirings of opto-coupler.
- Connect low impedance capacitor between the Vcc and GND terminal of each fast switching opto-coupler.
- Fast switching opto-couplers: tPLH, tPHL ≤ 0.8μs, Use High CMR type.
- Slow switching opto-coupler: CTR > 100%
- Use 6 isolated control power supplies (VD). Also, care should be taken to minimize the instantaneous voltage charge of the power supply.
- Make inductance of DC bus line as small as possible, and minimize surge voltage using snubber capacitor between P and N terminal.
- Use line noise filter capacitor (ex. 4.7nF) between each input AC line and ground to reject common-mode noise from AC line and improve noise immunity of the system.

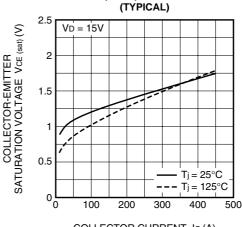


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PERFORMANCE CURVES

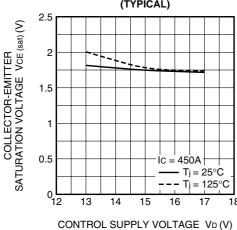


COLLECTOR-EMITTER SATURATION VOLTAGE (VS. Ic) CHARACTERISTICS

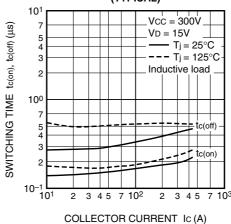


COLLECTOR CURRENT Ic (A)

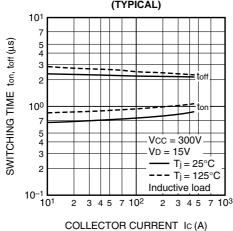
COLLECTOR-EMITTER SATURATION VOLTAGE (VS. VD) CHARACTERISTICS (TYPICAL)



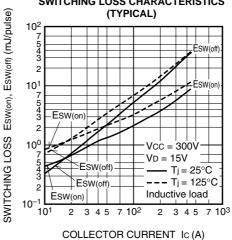
SWITCHING TIME CHARACTERISTICS (TYPICAL)



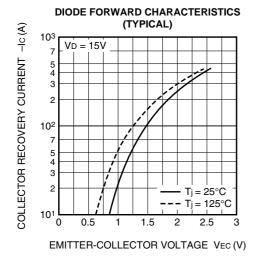
SWITCHING TIME CHARACTERISTICS (TYPICAL)

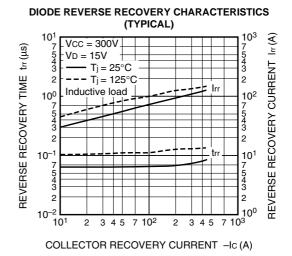


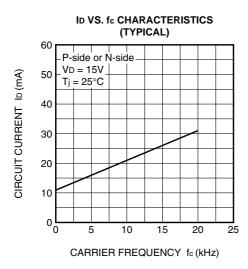
SWITCHING LOSS CHARACTERISTICS

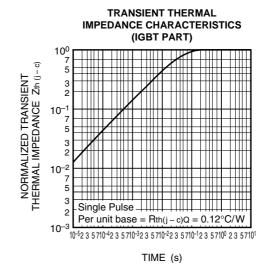


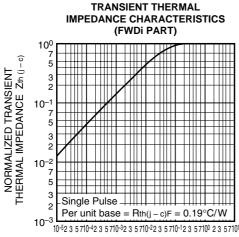
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TIME (s)

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